



Docket No.: M4065.0479/P479
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Stephen L. Casper et al.

Application No.: 10/076,486

Group Art Unit: 2818

Filed: February 19, 2002

Examiner: M. Tran

For: PROGRAMMABLE CONDUCTOR
RANDOM ACCESS MEMORY AND
METHOD FOR SENSING SAME

FOURTH INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
Washington, DC 20231

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO/SB/08. It is respectfully requested that the subject matter of the documents be expressly considered during the prosecution of this application and that the documents be made of record therein and appear among the "References Cited" on any patent to issue from this application. A copy of each document is attached.

Also attached is a copy of an International Search Report and of an International Preliminary Examination Report which issued in the corresponding international application. The cited documents have been provided to the Examiner in previously filed Information Disclosure Statements.

This Fourth Information Disclosure Statement is being filed concurrently with a Request for Continued Examination. While the application has been allowed, Applicants respectfully request that each reference included with this Fourth Information Disclosure Statement be fully considered.

Further, while the Notice of Allowance dated November 25, 2003 states that the Information Disclosure Statement filed September 16, 2003 has been considered, it is unclear from this statement whether only those references included in the Third Information Disclosure Statement filed September 16, 2003 were considered or whether, in addition to those references, the Examiner also considered the references included with the Information Disclosure Statement filed August 7, 2002 and the references included with the Second Information Disclosure Statement filed September 26, 2002 (copies of which, along with stamped postcard receipts, were enclosed with the Third Information Disclosure Statement filed September 16, 2003).

Applicants here again request that the Examiner initial the Forms 1449 enclosed with each of the original, Second and Third Information Disclosure Statements (copies of which are being refiled herewith for convenience). Applicants also request that the Examiner initial the Form 1449 being filed together with this Fourth Information Disclosure Statement.

In accordance with 37 C.F.R. § 1.97(g), the filing of this Fourth Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 C.F.R. § 1.56(a) exists. It is submitted that this Fourth Information Disclosure Statement is in compliance with 37 C.F.R. § 1.98 and the Examiner is respectfully requested to consider and cite the listed documents.

Dated: February 24, 2004

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No. 28,371

Salvatore P. Tamburo

Registration No. 45,153

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Attorneys for Applicants



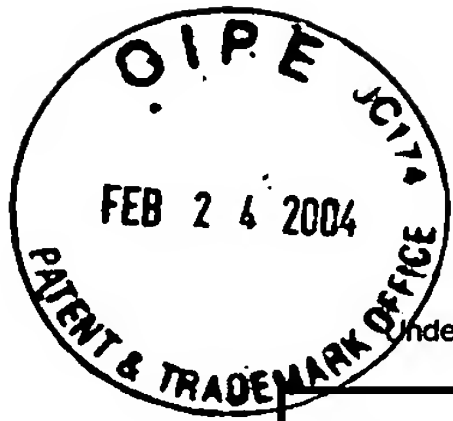
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

PTO/SB/08a/b (08-03)
Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>			Complete if Known		
			Application Number	10/076,486	
			Filing Date	February 19, 2002	
			First Named Inventor	Stephen L. Casper	
			Art Unit	2818	
			Examiner Name	M. Tran	
Sheet	1	of	2	Attorney Docket Number	M4065.0479/P479

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	DA	2002/0123169 A1	09/2002	Moore et al.	
	DB	2002/0123248 A1	09/2002	Moore et al.	
	DC	2002/0132417 A1	09/2002	Li	
	DD	2002/0168852 A1	11/2002	Harshfield et al.	
	DE	2002/0190289 A1	12/2002	Harshfield et al.	
	DF	2003/0032254 A1	02/2003	Gilton	
	DG	2003/0038301 A1	02/2003	Moore	
	DH	2003/0043631 A1	03/2003	Gilton et al.	
	DI	2003/0045049 A1	03/2003	Campbell et al.	
	DJ	2003/0045054 A1	03/2003	Campbell et al.	
	DK	2003/0047765 A1	03/2003	Campbell	
	DL	2003/0047772 A1	03/2003	Li	
	DM	2003/0047773 A1	03/2003	Li	
	DN	2003/0048519 A1	03/2003	Kozicki	
	DO	2003/0049912 A1	03/2003	Campbell et al.	
	DP	2003/0068861 A1	04/2003	Li et al.	
	DQ	2003/0068862 A1	04/2003	Li et al.	
	DR	2003/0095426 A1	05/2003	Hush et al.	
	DS	2003/0096497 A1	05/2003	Moore et al.	
	DT	2003/0107105 A1	06/2003	Kozicki	
	DU	2003/0117831 A1	06/2003	Hush	
	DV	2003/0128612 A1	07/2003	Moore et al.	
	DW	2003/0137869 A1	07/2003	Kozicki	
	DX	2003/0143782 A1	07/2003	Gilton et al.	
	DY	2003/0156447 A1	08/2003	Kozicki	
	DZ	2003/0156463 A1	08/2003	Casper et al.	
	DA'	6,473,332 B1	10/2002	Ignatiev et al.	
	DB'	5,851,882	12/1998	Harshfield	
	DC'	6,440,837 B1	08/2002	Harshfield	
	DD'	6,420,725 B1	07/2002	Harshfield	
	DE'	5,814,527	09/1998	Wolstenholme et al.	
	DF'	5,869,843	02/1999	Harshfield	
	DG'	2002/0160551 A1	10/2002	Harshfield	
	DH'	6,031,287	02/2000	Harshfield	
	DI'	5,818,749	10/1998	Harshfield	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				



Substitute for form 1449A/B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	10/076,486
				Filing Date	February 19, 2002
				First Named Inventor	Stephen L. Casper
				Art Unit	2818
				Examiner Name	M. Tran
Sheet	2	of	2	Attorney Docket Number	M4065.0479/P479

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials ²	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/076,486
				Filing Date	February 19, 2002
				First Named Inventor	Stephen L. Casper
				Art Unit	2818
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	M4065.0479/P479

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	AA	5,761,115	06/1998	Kozicki et al.	
	AB	5,896,312	04/1999	Kozicki et al.	
	AC	5,914,893	06/1999	Kozicki et al.	
	AD	6,084,796	07/2000	Kozicki et al.	
	AE	5,883,827	03/1999	Morgan	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Docket No.: M4065.0479/P479
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Stephen L. Casper et al.

Application No.: 10/076,486

Group Art Unit: 2818

Filed: February 19, 2002

Examiner: M. Tran

For: PROGRAMMABLE CONDUCTOR
RANDOM ACCESS MEMORY AND
METHOD FOR SENSING SAME

THIRD INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
Washington, DC 20231

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO/SB/08. It is respectfully requested that the subject matter of the documents be expressly considered during the prosecution of this application and that the documents be made of record therein and appear among the "References Cited" on any patent to issue from this application. A copy of each document is attached.

This Third Information Disclosure Statement is being filed concurrently with an Amendment.

A brief explanation of relevance of certain non-patent documents listed on Form PTO/SB/08 is provided and attached hereto as Appendix A. The brief explanation provided for each document is not tantamount to an admission that a document is "material" or that it qualifies as prior art. The Examiner is respectfully requested to utilize

Appendix A only as a tool by which to better categorize the documents for substantive use in examining the claims of the application.

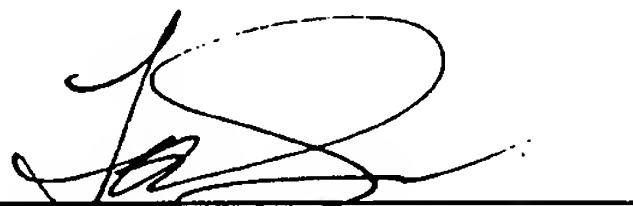
Documents discussed in Appendix A marked with an asterisk (*) are indicated to be potentially more relevant than others. Such marking is provided only to assist the Examiner; however, the Examiner is requested to thoroughly review all documents cited herein.

In accordance with 37 C.F.R. § 1.97(g), the filing of this Third Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 C.F.R. § 1.56(a) exists. It is submitted that this Third Information Disclosure Statement is in compliance with 37 C.F.R. § 1.98 and the Examiner is respectfully requested to consider and cite the listed documents.

The Director is hereby authorized to charge the \$180.00 fee as required by 37 C.F.R. §1.17(p) to the undersigned attorneys' credit card. Form PTO-2038 is attached. The Commissioner also is authorized to charge any deficiency in the fees filed, asserted to be filed, or which should have been filed herewith (or with any paper hereafter filed in this application by this firm), to our Deposit Account No. 04-1073, under Order No. M4065.0479/P479.

Dated: September 16, 2003

Respectfully submitted,

By 
Thomas J. D'Amico
Registration No. 28,371
Salvatore P. Tamburo
Registration No. 45,153
DICKSTEIN SHAPIRO MORIN &
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Attorneys for Applicants

Inventors: Stephen L. Casper et al.

Atty Docket No.: M4065.0479/P479 ✓

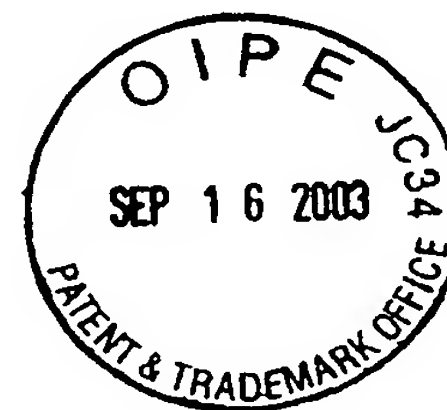
Application No.: 10/076,486

Filing Date: February 19, 2002

Title: PROGRAMMABLE CONDUCTOR RANDOM ACCESS MEMORY AND METHOD FOR SENSING SAME

Documents Filed:

Amendment w/copies 1449 and two date-stamped postcards
Third IDS w/Appendix A, PTO/SB/08A and 79 references
Form PTO-2038
Amendment Transmittal



Via: PTO Daily Run

Sender's Initials: TJD/SPT/rrl

Date: September 16, 2002

D.W.

Docket No.: M4065.0479/P479
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Stephen L. Casper et al.

Application No.: 10/076,486

Group Art Unit: 2818

Filed: February 19, 2002

Examiner: Not Known

For: PROGRAMMABLE CONDUCTOR
RANDOM ACCESS MEMORY AND
METHOD FOR SENSING SAME

SECOND INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
Washington, DC 20231

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO/SB/08. It is respectfully requested that the subject matter of the documents be expressly considered during the prosecution of this application and that the documents be made of record therein and appear among the "References Cited" on any patent to issue from this application. A copy of each document is attached.

A brief explanation of relevance of the non-patent documents listed on form PTO/SB/08 is provided and attached hereto as Appendix A. The brief explanation provided for each document is not tantamount to an admission that a document is "material" or that it qualifies as prior art. The Examiner is respectfully requested to utilize Appendix A only as a tool by which to better categorize the documents for substantive use in examining the claims of the application.


Documents discussed in Appendix A marked with an asterisk (*) are indicated to be potentially more relevant than others. Such marking is provided only to assist the Examiner; however, the Examiner is requested to thoroughly review all documents cited herein.

In accordance with 37 C.F.R. § 1.97(g), the filing of this Second Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 C.F.R. § 1.56(a) exists. It is submitted that the Second Information Disclosure Statement is in compliance with 37 C.F.R. § 1.98 and the Examiner is respectfully requested to consider and cite the listed documents.

The Commissioner is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0479/P479.

Dated: September 26, 2002

Respectfully submitted,

By 
Thomas J. D'Amico
Registration No. 28,371
Salvatore P. Tamburo
Registration No. 45,153
DICKSTEIN SHAPIRO MORIN &
OSHINSKY LLP
2101 L Street, N.W.
Washington, DC 20037-1526
(202) 785-9700
Attorneys for Applicant(s)

Atty Docket No... 4065.0479/P479 ✓

Inventors: Stephen L. Casper et al.

Application No.: 10/076,486

Filing Date: February 19, 2002

Title: PROGRAMMABLE CONDUCTOR RANDOM ACCESS MEMORY AND METHOD FOR SENSING SAME

Documents Filed:

Second Information Disclosure Statement w/Form PTO/SB/08A and 170 references



via: PTO Daily Run

Sender's Initials: TJD/SPT/rrl

Date: September 26, 2002

RAW 9/26/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Stephen L. Casper, et al.

Application No.: 10/076,486

Group Art Unit: 2818

Filed: February 19, 2002

Examiner: Not Yet Assigned

For: PROGRAMMABLE CONDUCTOR
RANDOM ACCESS MEMORY AND
METHOD FOR SENSING SAME

INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents
Washington, DC 20231

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08A. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed before the mailing date of a first Office Action on the merits as far as is known to the undersigned.

A copy of each reference on PTO/SB/08A is attached.

While the information and references disclosed in this Information Disclosure Statement may be "material" pursuant to 37 C.F.R. § 1.56, it is not intended to constitute an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that this Information Disclosure Statement is in compliance with 37 C.F.R. § 1.98 and the Examiner is respectfully requested to consider the listed references.

The Commissioner is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0479/P479. A duplicate copy of this paper is enclosed.

Dated: August 7, 2002

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

Salvatore P. Tamburo

Registration No.: 45,153

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Attorneys for Applicant

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete If Known	
				Application Number	10/076,486
				Filing Date	February 19, 2002
				First Named Inventor	Stephen L. Casper
				Art Unit	2818
				Examiner Name	M. Tran
Sheet	1	of	4	Attorney Docket Number	M4065.0479/P479

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	AA	6,469,364	10/2002	Kozicki	
	AB	2002/0168820 App.	11/2002	Kozicki	
	AC	2000/0072188 App	6/2002	Gilton	
	AD	2002/0123169 App	9/2002	Moore et al.	
	AE	2002/0123248 App.	9/2002	Moore et al.	
	AF	3,622,319	11/1971	Sharp	
	AG	3,743,847	7/1973	Boland	
	AH	4,269,935	5/1981	Masters et al.	
	AI	4,312,938	1/1982	Drexler, et al.	
	AJ	4,316,946	1/1982	Masters, et al.	
	AK	4,320,191	3/1982	Yoshikawa et al.	
	AL	4,405,710	9/1983	Balasubramanyam et al.	
	AM	4,419,421	12/1983	Wichelhaus, et al.	
	AN	4,795,657	1/1989	Formigoni et al.	
	AO	4,847,674	7/1989	Sliwa et al.	
	AP	4,499,557	2/1985	Holmberg et al.	
	AQ	5,177,567	1/1993	Klersy et al.	
	AR	5,219,788	6/1993	Abernathey et al.	
	AS	5,238,862	8/1993	Blalock et al.	
	AT	5,315,131	5/1994	Kishimoto et al.	
	AU	5,350,484	9/1994	Gardner et al.	
	AV	5,360,981	11/1994	Owen et al.	
	AW	5,512,328	4/1996	Yoshimura et al.	
	AX	5,512,773	4/1996	Wolf et al.	
	AY	5,726,083	3/1998	Takaishi	
	AA1	5,841,150	11/1998	Gonzalez et al.	
	AB1	5,846,889	12/1998	Harbison et al.	
	AC1	5,920,788	7/1999	Reinberg	
	AD1	5,998,066	12/1999	Block et al.	
	AE1	6,077,729	6/2000	Harshfield	
	AF1	6,117,720	9/2000	Harshfield	
	AG1	6,143,604	11/2000	Chiang et al.	
	AH1	6,177,338	1/2001	Liaw et al.	
	AI1	6,236,059	5/2001	Wolstenholme et al.	
	AJ1	6,297,170	10/2001	Gabriel et al.	
	AK1	6,300,684	10/2001	Gonzalez et al.	
	AL1	6,316,784	11/2001	Zahorik et al.	
	AM1	6,329,606	12/2001	Freyman et al.	
	AN1	6,350,679	2/2002	McDaniel et al.	
	AO1	6,376,284	4/2002	Gonzalez et al.	
	AP1	6,391,688	5/2002	Gonzalez et al.	
	AQ1	6,414,376	7/2002	Thakur et al.	
	AR1	6,423,628	7/2002	Li et al.	
	AS1	6,487,106	11/26/2002	Kozicki	
	AT1	5,314,772	5/24/1994	Kozicki	

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				First Named Inventor	Stephen L. Casper
				Art Unit	2818
				Examiner Name	M. Tran
Sheet	2	of	4	Attorney Docket Number	M4065.0479/P479

	AU1	2002/0190350 APP	12/19/2002	Kozicki	
	AV1	2003/0027416 APP	2/6/2003	Moore	
	AW1	2003/0001229 APP	1/2/2003	Moore et al.	
	AX1	2002/0106849 APP	8/8/2002	Moore.	
	AY1	2002/0127886 APP	9/12/2002	Moore et al.	
	AZ1	2002/0123170 APP	9/5/2002	Moore et al.	
	BA1	2002/0163828 APP	11/2002	Krieger et al	
	BB1	6,072,716	6/2000	Jacobson et al.	
	BC1	5,272,359	12/93	Nagasubramanian et al.	
	BD1	4,671,618	6/87	Wu et al.	
	BE1	4,800,526	1/89	Lewis	
	BF1	2003/0035314	02/20/03	Kozicki	
	BG1	2003/0035315	02/20/03	Kozicki	
	BH1	6,314,014	11/6/01	Lowrey et al.	
	BI1	5,883,827	3/16/99	Morgan	
	BJ1	4,112,512	9/5/78	Arzubi et al.	

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Sheet	3	of	4	Attorney Docket Number	M4065.0479/P479

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
	BA	JP 56126916	10/1981	Akira et al.		
	BB					

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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				Examiner Name	M. Tran
Sheet	4	of	4	Attorney Docket Number	M4065.0479/P479

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Inventor: Stephen L. Casper, et al.

Atty Docket No.: M4065.0479/P479

Application No.: 10/076,486

Filing Date: February 19, 2002

Title: PROGRAMMABLE CONDUCTOR RANDOM ACCESS MEMORY AND METHOD FOR SENSING SAME

Documents Filed:

Transmittal (1 page)

Information Disclosure Statement (4 pages; 2 copies)

Form PTO/SB/08A (1 page)

5 U.S. Patent References



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				First Named Inventor	Stephen L. Casper
				Art Unit	2818
				Examiner Name	Not Known
Sheet	1	of	8	Attorney Docket Number	M4065.0479/P479

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Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	AB	US 2002/0000666	01/03/2002	Kozicki et al.	
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
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	BB	WO 00/48196	08/17/2000	Kozicki et al.		
	BC	WO 97/48032	12/18/1997	Kozicki et al.		
	BD	WO 99/28914	06/10/1999	Kozicki et al.		

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